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STMicroelectronics 2STC5200

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High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} > 230V
- Complementary to 2STA1943
- Fast-switching speed
- Typical f_T = 30 MHz

Application

Audio power amplifier

Description

This device is a NPN transistor manufactured using new BiT-LA (Bipolar Transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

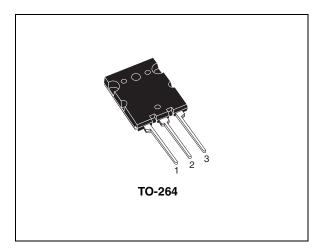


Figure 1. Internal schematic diagram

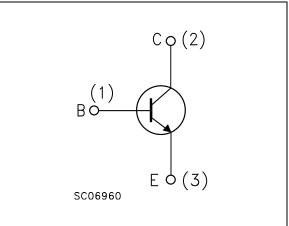


Table 1.Device summary

Order code	Marking	Package	Packaging
2STC5200	2STC5200	TO-264	Tube



Electrical ratings

2STC5200

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0) 230		V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	230	V
V _{EBO}	Emitter-base voltage $(I_C = 0)$	5	V
۱ _C	Collector current	15	А
I _{CM}	Collector peak current	30	А
P _{tot}	Total dissipation at $T_{C} = 25^{\circ}C$	150	W
T _{stg}	Storage temperature	-55 to 150	°C
TJ	Operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thJ-case}	Thermal resistance junction-case Max	0.83	°C/W



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2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics					
Parameter	Test conditions	Min.	Тур.	Max.	Unit
Collector cut-off current (I _E = 0)	V _{CB} = 230 V			5	μA
Emitter cut-off current (I _C = 0)	V _{EB} = 5 V			5	μA
Collector-emitter breakdown voltage ($I_B = 0$)	I _C = 50 mA	230			V
Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA	230			V
Emitter-base breakdown voltage (I _C = 0)	I _E =1 mA	5			v
Collector-emitter saturation voltage	I _C = 8 A I _B = 800 mA			3	v
Base-emitter voltage	$I_{\rm C} = 7 \ {\rm A}$ $V_{\rm CE} = 5 \ {\rm V}$			1.5	V
DC current gain	$I_{C} = 1 A$ $V_{CE} = 5 V$ $I_{C} = 7 A$ $V_{CE} = 5 V$	80 35		160	
Resistive load Turn-on time Storage time Fall time	$V_{CC} = 60 V I_C = 5A$ $I_{B1} = -I_{B2} = 0.5 A$		0.24 4.7 0.6		µs µs µs
Transition frequency	$I_{\rm C} = 1 \ {\rm A}$ $V_{\rm CE} = 5 \ {\rm V}$		30		MHz
Collector-base capacitance (I _E = 0)	V _{CB} = 10 V f = 1 MHz		150		pF
	ParameterCollector cut-off current $(I_E = 0)$ Emitter cut-off current $(I_C = 0)$ Collector-emitter breakdown voltage $(I_B = 0)$ Collector-base breakdown voltage $(I_E = 0)$ Emitter-base breakdown voltage $(I_C = 0)$ Collector-emitter saturation voltageBase-emitter voltageDC current gainResistive load Turn-on time Storage time Fall timeTransition frequencyCollector-base capacitance	ParameterTest conditionsCollector cut-off current $(I_E = 0)$ $V_{CB} = 230 \text{ V}$ Emitter cut-off current $(I_C = 0)$ $V_{EB} = 5 \text{ V}$ Collector-emitter breakdown voltage $(I_B = 0)$ $I_C = 50 \text{ mA}$ Collector-base breakdown voltage $(I_E = 0)$ $I_C = 100 \mu \text{A}$ Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 100 \mu \text{A}$ Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 1 \text{ mA}$ Collector-emitter saturation voltage $I_C = 7 \text{ A} V_{CE} = 5 \text{ V}$ DC current gain $I_C = 7 \text{ A} V_{CE} = 5 \text{ V}$ DC current gain $V_{CC} = 60 \text{ V} I_C = 5 \text{ V}$ Resistive load Turn-on time Storage time Fall time $V_{CC} = 1 \text{ A} V_{CE} = 5 \text{ V}$ Transition frequency $I_C = 1 \text{ A} V_{CE} = 5 \text{ V}$ Collector-base capacitance $V_{CR} = 10 \text{ V} f = 1 \text{ MHz}$	ParameterTest conditionsMin.Collector cut-off current $(I_E = 0)$ $V_{CB} = 230 \text{ V}$ Emitter cut-off current $(I_C = 0)$ $V_{EB} = 5 \text{ V}$ Collector-emitter breakdown voltage $(I_B = 0)$ $I_C = 50 \text{ mA}$ 230Collector-base breakdown voltage $(I_E = 0)$ $I_C = 100 \mu A$ 230Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 100 \mu A$ 230Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 1 \text{ MA}$ 5Collector-emitter saturation voltage $I_C = 8 \text{ A}$ $I_B = 800 \text{ mA}$ Base-emitter voltage $I_C = 7 \text{ A}$ $V_{CE} = 5 \text{ V}$ DC current gain $I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ V}$ Resistive load Turn-on time Fall time $V_{CC} = 60 \text{ V}$ $I_C = 5 \text{ A}$ Transition frequency $I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ V}$ Collector-base capacitance Voer = 10 V $I_C = 1 \text{ MHz}$	ParameterTest conditionsMin.Typ.Collector cut-off current $(I_E = 0)$ $V_{CB} = 230 \text{ V}$ \square \square Emitter cut-off current $(I_C = 0)$ $V_{EB} = 5 \text{ V}$ \square \square Collector-emitter breakdown voltage $(I_B = 0)$ $I_C = 50 \text{ mA}$ 230 \square Collector-base breakdown voltage $(I_C = 0)$ $I_C = 100 \mu \text{A}$ 230 \square Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 100 \mu \text{A}$ 230 \square Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 1 \text{ MA}$ 5 \square Collector-emitter saturation voltage $I_C = 8 \text{ A}$ $I_B = 800 \text{ mA}$ \square Base-emitter voltage $I_C = 7 \text{ A}$ $V_{CE} = 5 \text{ V}$ $B0$ DC current gain $I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ V}$ $B0$ Resistive load Turn-on time Fall time $V_{CC} = 60 \text{ V}$ $I_C = 5A$ 0.24 Transition frequency $I_C = 1 \text{ A}$ $V_{CE} = 5 \text{ V}$ 30 Collector-base capacitance $V_{CR} = 10 \text{ V}$ $I = 1 \text{ MHZ}$ $I = 50$	ParameterTest conditionsMin.Typ.Max.Collector cut-off current $(I_E = 0)$ $V_{CB} = 230 V$ I S Emitter cut-off current $(I_C = 0)$ $V_{EB} = 5 V$ I S Collector-emitter breakdown voltage $(I_B = 0)$ $I_C = 50 \text{ mA}$ 230 I Collector-base breakdown voltage $(I_E = 0)$ $I_C = 100 \mu A$ 230 I Emitter-base breakdown voltage $(I_C = 0)$ $I_C = 100 \mu A$ 230 I Collector-emitter saturation voltage $(I_C = 0)$ $I_C = 8 A I_B = 800 \text{ mA}$ S I Collector-emitter saturation voltage $I_C = 7 A V_{CE} = 5 V$ S I DC current gain $I_C = 1 A V_{CE} = 5 V$ 80 $I_C = 7 A V_{CE} = 5 V$ S $I60$ Resistive load Turn-on time Fall time $V_{CC} = 60 V I_C = 5A$ $I_B = -1_{B2} = 0.5 A$ 0.24 4.7 0.6 0.24 4.7 0.6 Transition frequency $I_C = 1 A V_{CE} = 5 V$ 30 I

Table 4. Electrical characteristics

1. Pulsed: pulse duration = 300 μ s, duty cycle $\leq 1.5\%$



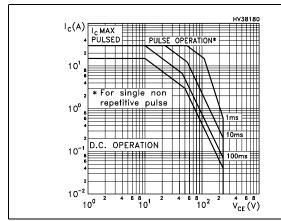
Electrical characteristics

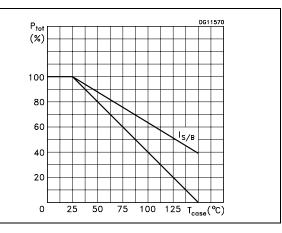
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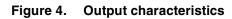
2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve







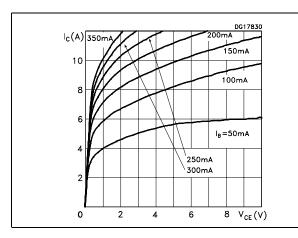


Figure 5. DC current gain

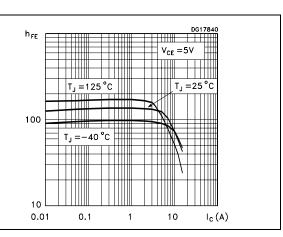
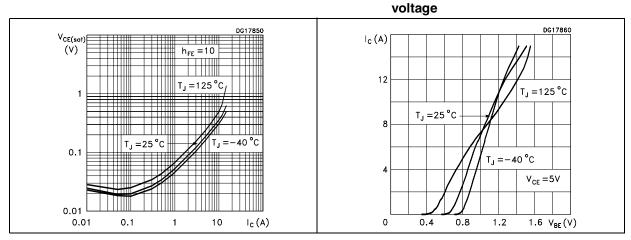


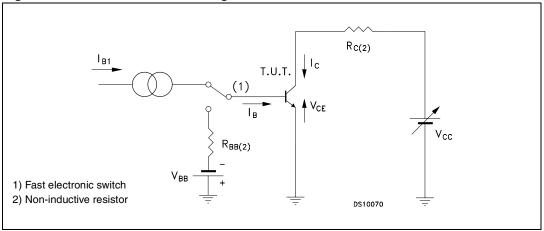
Figure 6. Collector-emitter saturation voltage Figure 7. Collector current vs base-emitter





2.2 Test circuit

Figure 8. Resistive load switching test circuit







Package mechanical data

2STC5200

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3 Package mechanical data

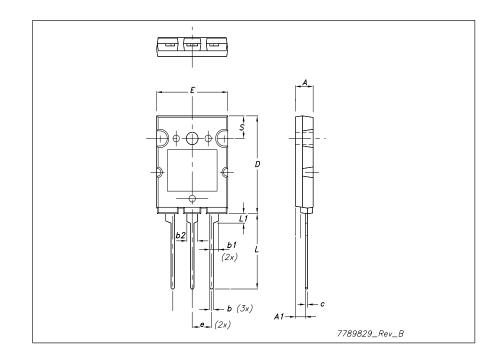
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Package mechanical data

	TO-264 Mechanical data		
Dim.		mm.	
	Min.	Тур	Max.
A	4.80		5.20
A1	2.50		3.10
b	0.90	1.0	1.25
b1		2.5	
b2		2.8	
с	0.50	0.60	0.85
D	25.6		26.4
E	19.80		20.20
е	5.15		5.75
L	19.50		20.50
L1	2.30		2.70
øP	3.55		3.65







Revision history

2STC5200

4 **Revision history**

Table 5. Document revision history

Date	Revision	Changes
19-Jun-2007	1	Initial release.
11-Dec-2007	2	Document promoted from preliminary data to datasheet.





Revision history

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